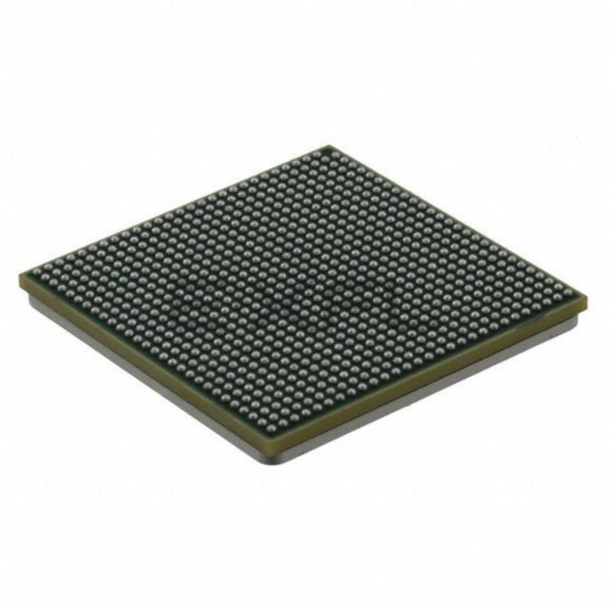

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8543vuaqg

- Memory prefetching of PCI read accesses
- Supports posting of processor-to-PCI and PCI-to-memory writes
- PCI 3.3-V compatible
- Selectable hardware-enforced coherency

• Serial RapidIO™ interface unit
  - Supports *RapidIO™ Interconnect Specification, Revision 1.2*
  - Both 1× and 4× LP-serial link interfaces
  - Long- and short-haul electricals with selectable pre-compensation
  - Transmission rates of 1.25, 2.5, and 3.125 Gbaud (data rates of 1.0, 2.0, and 2.5 Gbps) per lane
  - Auto detection of 1- and 4-mode operation during port initialization
  - Link initialization and synchronization
  - Large and small size transport information field support selectable at initialization time
  - 34-bit addressing
  - Up to 256 bytes data payload
  - All transaction flows and priorities
  - Atomic set/clr/inc/dec for read-modify-write operations
  - Generation of IO_READ_HOME and FLUSH with data for accessing cache-coherent data at a remote memory system
  - Receiver-controlled flow control
  - Error detection, recovery, and time-out for packets and control symbols as required by the RapidIO specification
  - Register and register bit extensions as described in part VIII (Error Management) of the RapidIO specification
  - Hardware recovery only
  - Register support is not required for software-mediated error recovery.
  - Accept-all mode of operation for fail-over support
  - Support for RapidIO error injection
  - Internal LP-serial and application interface-level loopback modes
  - Memory and PHY BIST for at-speed production test

• RapidIO-compatible message unit
  - 4 Kbytes of payload per message
  - Up to sixteen 256-byte segments per message
  - Two inbound data message structures within the inbox
  - Capable of receiving three letters at any mailbox
  - Two outbound data message structures within the outbox
  - Capable of sending three letters simultaneously
  - Single segment multicast to up to 32 devIDs
  - Chaining and direct modes in the outbox

Table 13 provides the recommended operating conditions for the DDR SDRAM controller when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.15$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.15$	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 \text{ V} \leq V_{OUT} \leq GV_{DD}$.

Table 14 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

Table 19. DDR SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[*n*] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the MDQS override bits (called WR_DATA_DELAY) in the TIMING_CFG_2 register. This is typically set to the same delay as in DDR_SDRAM_CLK_CNTL[CLK_ADJUST]. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8548E PowerQUICC III Integrated Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe must be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[*n*] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

NOTE

For the ADDR/CMD setup and hold specifications in Table 19, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.

Figure 3 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

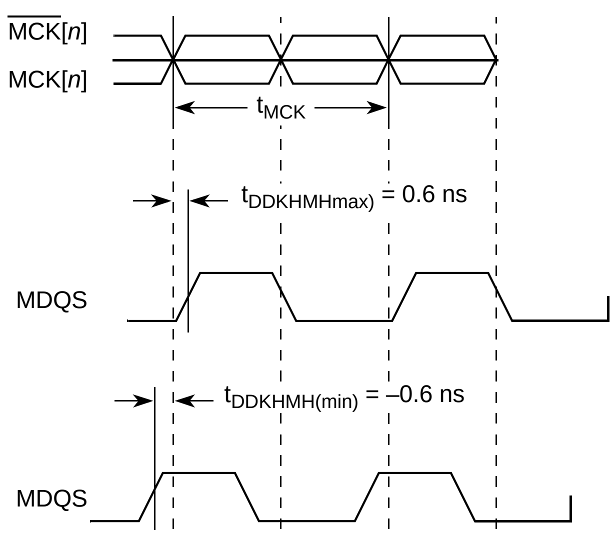


Figure 3. Timing Diagram for tDDKHMH

10.2 Local Bus AC Electrical Specifications

This table describes the timing parameters of the local bus interface at BV_{DD} = 3.3 V. For information about the frequency range of local bus, see Section 20.1, “Clock Ranges.”

Table 40. Local Bus Timing Parameters (BV_{DD} = 3.3 V)—PLL Enabled

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIVKH1}$	1.8	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.0	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.2	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.3	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.3	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.7	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to 0.4 × BV_{DD} of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[*n*]. Skew measured between complementary signals at $BV_{DD}/2$.
8. Guaranteed by design.

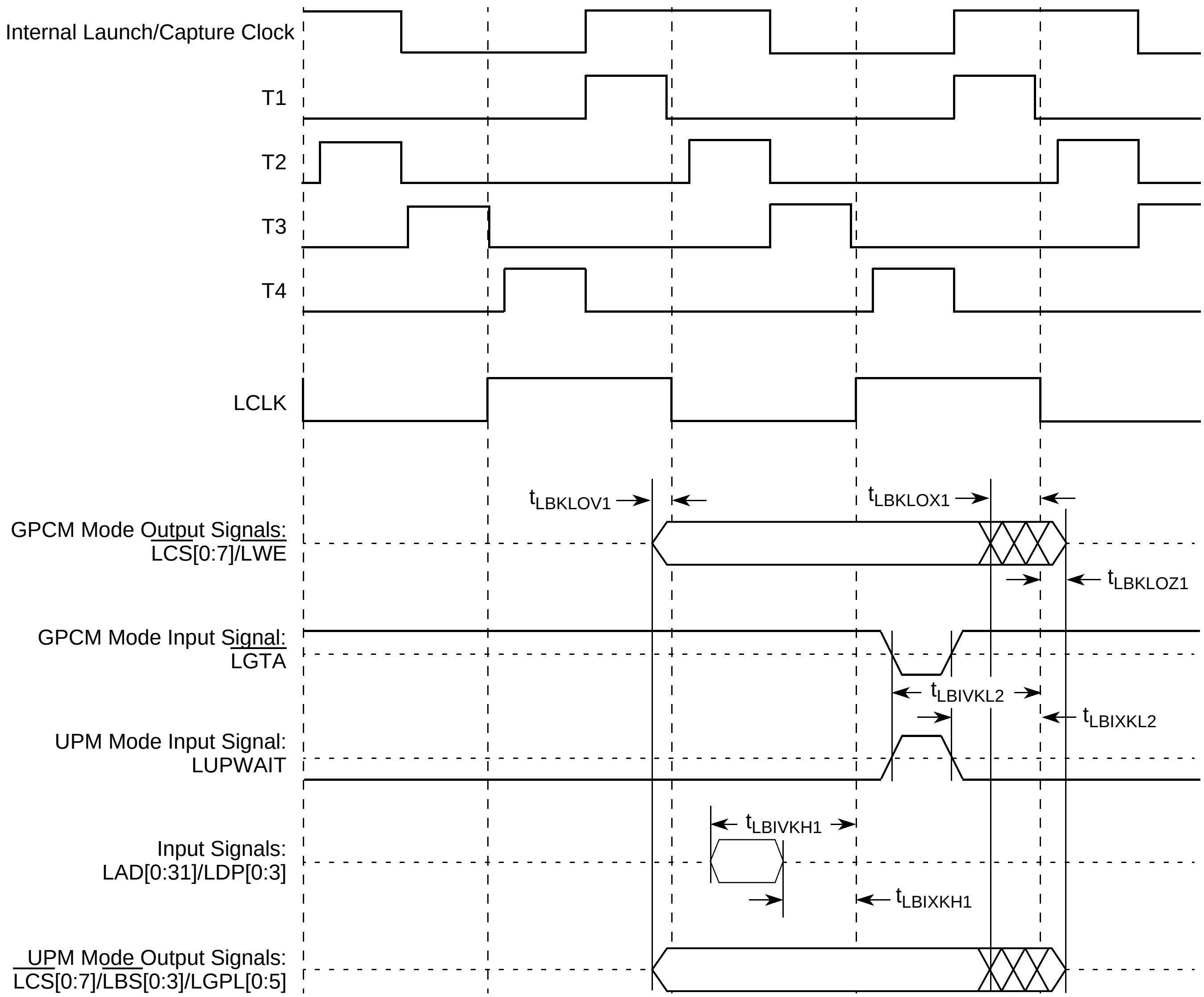


Figure 28. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Bypass Mode)

11 Programmable Interrupt Controller

In IRQ edge trigger mode, when an external interrupt signal is asserted (according to the programmed polarity), it must remain the assertion for at least 3 system clocks (SYSCLK periods).

12 JTAG

This section describes the DC and AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

12.1 JTAG DC Electrical Characteristics

This table provides the DC electrical characteristics for the JTAG interface.

Table 43. JTAG DC Electrical Characteristics

Parameter	Symbol[1]	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN}[1] = 0 V or $V_{IN} = V_{DD}$)	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN}.

12.2 JTAG AC Electrical Specifications

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 32.

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK)[1]

Parameter	Symbol[2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	6
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t_{JTDVKH} t_{JTIVKH}	4 0	— —	ns	4
Input hold times: Boundary-scan data TMS, TDI	t_{JTDXKH} t_{JTIXKH}	20 25	— —	ns	4

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK)[1] (continued)

Parameter	Symbol[2]	Min	Max	Unit	Notes
Valid times: Boundary-scan data TDO	t_{JTKLDV} t_{JTKLOV}	4 2	20 10	ns	5
Output hold times: Boundary-scan data TDO	t_{JTKLDX} t_{JTKLOX}	30 30	— —	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	t_{JTKLDZ} t_{JTKLOZ}	3 3	19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 29). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design.

Figure 29 provides the AC test load for TDO and the boundary-scan outputs.

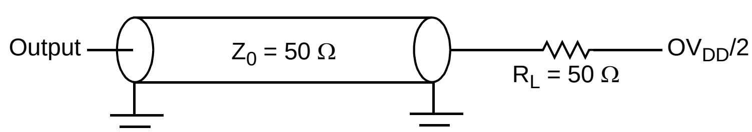


Figure 29. AC Test Load for the JTAG Interface

Figure 30 provides the JTAG clock input timing diagram.

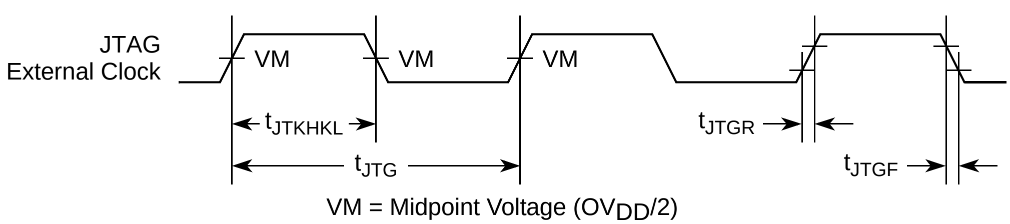


Figure 30. JTAG Clock Input Timing Diagram

13 I2C

This section describes the DC and AC electrical characteristics for the I2C interfaces of the device.

13.1 I2C DC Electrical Characteristics

This table provides the DC electrical characteristics for the I2C interfaces.

Table 45. I2C DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	2
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max))	I_I	–10	10	μA	3
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. See the *MPC8548E PowerQUICC™ III Integrated Processor Family Reference Manual*, for information on the digital filter used.
3. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

13.2 I2C AC Electrical Specifications

This table provides the AC timing parameters for the I2C interfaces.

Table 46. I2C AC Electrical Specifications

Parameter	Symbol[1]	Min	Max	Unit	Notes
SCL clock frequency	f_{I2C}	0	400	kHz	—
Low period of the SCL clock	t_{I2CL}	1.3	—	μs	4
High period of the SCL clock	t_{I2CH}	0.6	—	μs	4
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs	4
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs	4
Data setup time	t_{I2DVKH}	100	—	ns	4
Data input hold time: CBUS compatible masters I2C bus devices	t_{I2DXKL}	 — 0	 — —	μs	2
Data output delay time:	t_{I2OVKL}	—	0.9	—	3
Set-up time for STOP condition	t_{I2PVKH}	0.6	—	μs	—
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs	—

This table provides the PCI AC timing specifications at 66 MHz.

Table 52. PCI AC Timing Specifications at 66 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
CLK to output valid	t_{PCKHOV}	—	6.0	ns	2, 3
Output hold from CLK	t_{PCKHOX}	2.0	—	ns	2, 10
CLK to output high impedance	t_{PCKHOZ}	—	14	ns	2, 4, 11
Input setup to CLK	t_{PCIVKH}	3.0	—	ns	2, 5, 10
Input hold from CLK	t_{PCIXKH}	0	—	ns	2, 5, 10
$\overline{\text{REQ64}}$ to $\overline{\text{HRESET}}$ [9] setup time	t_{PCRVRH}	$10 \times t_{SYS}$	—	clocks	6, 7, 11
$\overline{\text{HRESET}}$ to $\overline{\text{REQ64}}$ hold time	t_{PCRHRX}	0	50	ns	7, 11
$\overline{\text{HRESET}}$ high to first $\overline{\text{FRAME}}$ assertion	t_{PCRHFV}	10	—	clocks	8, 11

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI/PCI-X timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the SYSCLK clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI/PCI-X timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.2 Local Bus Specifications*.
3. All PCI signals are measured from $OV_{DD}/2$ of the rising edge of SYSCLK or PCI_CLK*n* to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V PCI signaling levels.
4. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Input timings are measured at the pin.
6. The timing parameter t_{SYS} indicates the minimum and maximum CLK cycle times for the various specified frequencies. The system clock period must be kept within the minimum and maximum defined ranges. For values see Section 20, “Clocking.”
7. The setup and hold time is with respect to the rising edge of $\overline{\text{HRESET}}$.
8. The timing parameter t_{PCRHFV} is a minimum of 10 clocks rather than the minimum of 5 clocks in the *PCI 2.2 Local Bus Specifications*.
9. The reset assertion timing requirement for $\overline{\text{HRESET}}$ is 100 μs.
10. Guaranteed by characterization.
11. Guaranteed by design.

Figure 35 provides the AC test load for PCI and PCI-X.

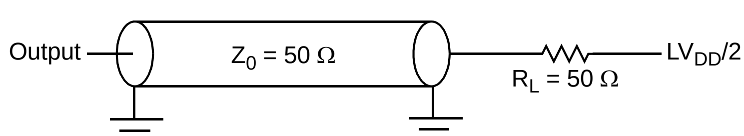


Figure 35. PCI/PCI-X AC Test Load

Table 53. PCI-X AC Timing Specifications at 66 MHz (continued)

Parameter	Symbol	Min	Max	Unit	Notes
$\overline{\text{HRESET}}$ to PCI-X initialization pattern hold time	t_{PCRHIX}	0	50	ns	6, 11

Notes:

1. See the timing measurement conditions in the *PCI-X 1.0a Specification*.
2. Minimum times are measured at the package pin (not the test point). Maximum times are measured with the test point and load circuit.
3. Setup time for point-to-point signals applies to $\overline{\text{REQ}}$ and $\overline{\text{GNT}}$ only. All other signals are bused.
4. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Setup time applies only when the device is not driving the pin. Devices cannot drive and receive signals at the same time.
6. Maximum value is also limited by delay to the first transaction (time for $\overline{\text{HRESET}}$ high to first configuration access, t_{PCRHFV}). The PCI-X initialization pattern control signals after the rising edge of $\overline{\text{HRESET}}$ must be negated no later than two clocks before the first $\overline{\text{FRAME}}$ and must be floated no later than one clock before $\overline{\text{FRAME}}$ is asserted.
7. A PCI-X device is permitted to have the minimum values shown for t_{PCKHOV} and t_{CYC} only in PCI-X mode. In conventional mode, the device must meet the requirements specified in PCI 2.2 for the appropriate clock frequency.
8. Device must meet this specification independent of how many outputs switch simultaneously.
9. The timing parameter t_{PCRHFV} is a minimum of 10 clocks rather than the minimum of 5 clocks in the *PCI-X 1.0a Specification.*
10. Guaranteed by characterization.
11. Guaranteed by design.

This table provides the PCI-X AC timing specifications at 133 MHz. Note that the maximum PCI-X frequency in synchronous mode is 110 MHz.

Table 54. PCI-X AC Timing Specifications at 133 MHz

Parameter	Symbol	Min	Max	Unit	Notes
SYSCLK to signal valid delay	t_{PCKHOV}	—	3.8	ns	1, 2, 3, 7, 8
Output hold from SYSCLK	t_{PCKHOX}	0.7	—	ns	1, 11
SYSCLK to output high impedance	t_{PCKHOZ}	—	7	ns	1, 4, 8, 12
Input setup time to SYSCLK	t_{PCIVKH}	1.2	—	ns	3, 5, 9, 11
Input hold time from SYSCLK	t_{PCIXKH}	0.5	—	ns	11
$\overline{\text{REQ64}}$ to $\overline{\text{HRESET}}$ setup time	t_{PCRVRH}	10	—	clocks	12
$\overline{\text{HRESET}}$ to $\overline{\text{REQ64}}$ hold time	t_{PCRHRX}	0	50	ns	12
$\overline{\text{HRESET}}$ high to first $\overline{\text{FRAME}}$ assertion	t_{PCRHFV}	10	—	clocks	10, 12
PCI-X initialization pattern to $\overline{\text{HRESET}}$ setup time	t_{PCIVRH}	10	—	clocks	12

Table 56. Differential Transmitter (TX) Output Specifications

Symbol	Parameter	Min	Nom	Max	Unit	Comments
UI	Unit interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for spread spectrum clock dictated variations. See Note 1.
$V_{TX\text{-}DIFFp\text{-}p}$	Differential peak-to-peak output voltage	0.8	—	1.2	V	$V_{TX\text{-}DIFFp\text{-}p} = 2 \times \lvert V_{TX\text{-}D+} - V_{TX\text{-}D-}\rvert$. See Note 2.
$V_{TX\text{-}DE\text{-}RATIO}$	De- emphasized differential output voltage (ratio)	–3.0	–3.5	–4.0	dB	Ratio of the $V_{TX\text{-}DIFFp\text{-}p}$ of the second and following bits after a transition divided by the $V_{TX\text{-}DIFFp\text{-}p}$ of the first bit after a transition. See Note 2.
$T_{TX\text{-}EYE}$	Minimum TX eye width	0.70	—	—	UI	The maximum transmitter jitter can be derived as $T_{TX\text{-}MAX\text{-}JITTER} = 1 - T_{TX\text{-}EYE} = 0.3$ UI. See Notes 2 and 3.
$T_{TX\text{-}EYE\text{-}MEDIAN\text{-}to\text{-}MAX\text{-}JITTER}$	Maximum time between the jitter median and maximum deviation from the median.	—	—	0.15	UI	Jitter is defined as the measurement variation of the crossing points ($V_{TX\text{-}DIFFp\text{-}p} = 0$ V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2 and 3.
$T_{TX\text{-}RISE}$, $T_{TX\text{-}FALL}$	D+/D– TX output rise/fall time	0.125	—	—	UI	See Notes 2 and 5.
$V_{TX\text{-}CM\text{-}ACp}$	RMS AC peak common mode output voltage	—	—	20	mV	$V_{TX\text{-}CM\text{-}ACp} = \text{RMS}(\lvert V_{TXD+} + V_{TXD-}\rvert/2 - V_{TX\text{-}CM\text{-}DC})$ $V_{TX\text{-}CM\text{-}DC} = DC_{(avg)}$ of $\lvert V_{TX\text{-}D+} + V_{TX\text{-}D-}\rvert/2$. See Note 2.
$V_{TX\text{-}CM\text{-}DC\text{-}ACTIVE\text{-}IDLE\text{-}DELTA}$	Absolute delta of dc common mode voltage during L0 and electrical idle	0	—	100	mV	$\lvert V_{TX\text{-}CM\text{-}DC\ (during\ L0)} + V_{TX\text{-}CM\text{-}Idle\text{-}DC\ (during\ electrical\ idle)}\rvert \le 100$ mV $V_{TX\text{-}CM\text{-}DC} = DC_{(avg)}$ of $\lvert V_{TX\text{-}D+} + V_{TX\text{-}D-}\rvert/2$ [L0] $V_{TX\text{-}CM\text{-}Idle\text{-}DC} = DC_{(avg)}$ of $\lvert V_{TX\text{-}D+} + V_{TX\text{-}D-}\rvert/2$ [electrical idle] See Note 2.
$V_{TX\text{-}CM\text{-}DC\text{-}LINE\text{-}DELTA}$	Absolute delta of DC common mode between D+ and D–	0	—	25	mV	$\lvert V_{TX\text{-}CM\text{-}DC\text{-}D+} - V_{TX\text{-}CM\text{-}DC\text{-}D-}\rvert \le 25$ mV $V_{TX\text{-}CM\text{-}DC\text{-}D+} = DC_{(avg)}$ of $\lvert V_{TX\text{-}D+}\rvert$ $V_{TX\text{-}CM\text{-}DC\text{-}D-} = DC_{(avg)}$ of $\lvert V_{TX\text{-}D-}\rvert$. See Note 2.
$V_{TX\text{-}IDLE\text{-}DIFFp}$	Electrical idle differential peak output voltage	0	—	20	mV	$V_{TX\text{-}IDLE\text{-}DIFFp} = \lvert V_{TX\text{-}IDLE\text{-}D+} - V_{TX\text{-}IDLE\text{-}D-}\rvert \le 20$ mV. See Note 2.
$V_{TX\text{-}RCV\text{-}DETECT}$	The amount of voltage change allowed during receiver detection	—	—	600	mV	The total amount of voltage change that a transmitter can apply to sense whether a low impedance receiver is present. See Note 6.

18.5 Explanatory Note on Transmitter and Receiver Specifications

AC electrical specifications are given for transmitter and receiver. Long- and short-run interfaces at three baud rates (a total of six cases) are described.

The parameters for the AC electrical specifications are guided by the XAUI electrical interface specified in Clause 47 of IEEE 802.3ae-2002.

XAUI has similar application goals to Serial RapidIO, as described in Section 8.1. The goal of this standard is that electrical designs for Serial RapidIO can reuse electrical designs for XAUI, suitably modified for applications at the baud intervals and reaches described herein.

18.6 Transmitter Specifications

LP-serial transmitter electrical and timing specifications are stated in the text and tables of this section.

The differential return loss, S11, of the transmitter in each case shall be better than:

- –10 dB for (baud frequency)/10 < Freq(f) < 625 MHz, and
- –10 dB + 10log(f/625 MHz) dB for 625 MHz ≤ Freq(f) ≤ baud frequency

The reference impedance for the differential return loss measurements is 100-Ω resistive. Differential return loss includes contributions from on-chip circuitry, chip packaging, and any off-chip components related to the driver. The output impedance requirement applies to all valid output levels.

It is recommended that the 20%–80% rise/fall time of the transmitter, as measured at the transmitter output, in each case have a minimum value 60 ps.

It is recommended that the timing skew at the output of an LP-serial transmitter between the two signals that comprise a differential pair not exceed 25 ps at 1.25 GB, 20 ps at 2.50 GB, and 15 ps at 3.125 GB.

Table 59. Short Run Transmitter AC Timing Specifications—1.25 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output voltage	V_O	–0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V_{DIFFPP}	500	1000	mV p-p	—
Deterministic jitter	J_D	—	0.17	UI p-p	—
Total jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	800	800	ps	±100 ppm

Table 68. Receiver AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential input voltage	V_{IN}	200	1600	mVp-p	Measured at receiver
Deterministic jitter tolerance	J_D	0.37	—	UI p-p	Measured at receiver
Combined deterministic and random jitter tolerance	J_{DR}	0.55	—	UI p-p	Measured at receiver
Total jitter tolerance[1]	J_T	0.65	—	UI p-p	Measured at receiver
Multiple input skew	S_{MI}	—	22	ns	Skew at the receiver input between lanes of a multilane link
Bit error rate	BER	—	10^{-12}		—
Unit interval	UI	320	320	ps	±100 ppm

Note:
1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 53. The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.

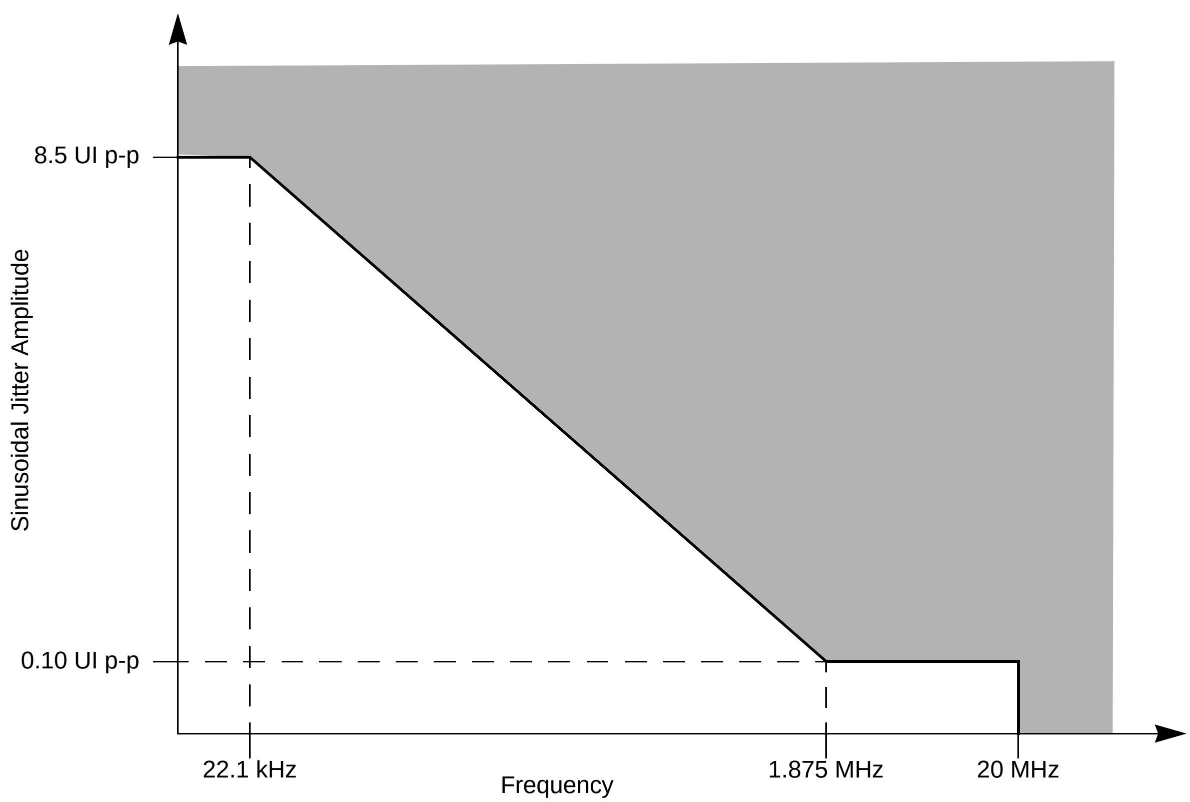


Figure 53. Single Frequency Sinusoidal Jitter Limits

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Three-Speed Ethernet Controller (Gigabit Ethernet 2)				
TSEC2_RXD[7:0]	P2, R2, N1, N2, P3, M2, M1, N3	I	LV_{DD}	—
TSEC2_TXD[7:0]	N9, N10, P8, N7, R9, N5, R8, N6	O	LV_{DD}	5, 9, 33
TSEC2_COL	P1	I	LV_{DD}	—
TSEC2_CRS	R6	I/O	LV_{DD}	20
TSEC2_GTX_CLK	P6	O	LV_{DD}	
TSEC2_RX_CLK	N4	I	LV_{DD}	—
TSEC2_RX_DV	P5	I	LV_{DD}	—
TSEC2_RX_ER	R1	I	LV_{DD}	—
TSEC2_TX_CLK	P10	I	LV_{DD}	—
TSEC2_TX_EN	P7	O	LV_{DD}	30
TSEC2_TX_ER	R10	O	LV_{DD}	5, 9, 33
Three-Speed Ethernet Controller (Gigabit Ethernet 3)				
TSEC3_TXD[3:0]	V8, W10, Y10, W7	O	TV_{DD}	5, 9, 29
TSEC3_RXD[3:0]	Y1, W3, W5, W4	I	TV_{DD}	—
TSEC3_GTX_CLK	W8	O	TV_{DD}	—
TSEC3_RX_CLK	W2	I	TV_{DD}	—
TSEC3_RX_DV	W1	I	TV_{DD}	—
TSEC3_RX_ER	Y2	I	TV_{DD}	—
TSEC3_TX_CLK	V10	I	TV_{DD}	—
TSEC3_TX_EN	V9	O	TV_{DD}	30
Three-Speed Ethernet Controller (Gigabit Ethernet 4)				
TSEC4_TXD[3:0]/TSEC3_TXD[7:4]	AB8, Y7, AA7, Y8	O	TV_{DD}	1, 5, 9, 29
TSEC4_RXD[3:0]/TSEC3_RXD[7:4]	AA1, Y3, AA2, AA4	I	TV_{DD}	1
TSEC4_GTX_CLK	AA5	O	TV_{DD}	—
TSEC4_RX_CLK/TSEC3_COL	Y5	I	TV_{DD}	1
TSEC4_RX_DV/TSEC3_CRS	AA3	I/O	TV_{DD}	1, 31
TSEC4_TX_EN/TSEC3_TX_ER	AB6	O	TV_{DD}	1, 30
DUART				
$\overline{\text{UART\_CTS}}$[0:1]	AB3, AC5	I	OV_{DD}	—
$\overline{\text{UART\_RTS}}$[0:1]	AC6, AD7	O	OV_{DD}	—
UART_SIN[0:1]	AB5, AC7	I	OV_{DD}	—
UART_SOUT[0:1]	AB7, AD8	O	OV_{DD}	—

Table 72. MPC8547E Pinout Listing (continued)

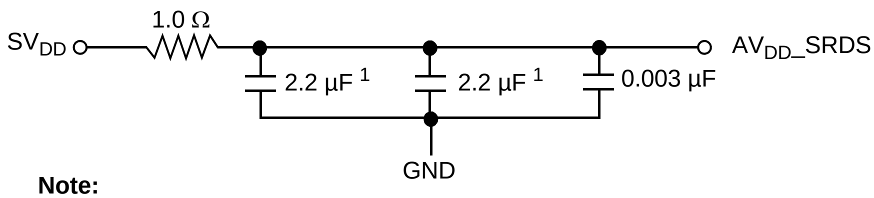
Signal	Package Pin Number	Pin Type	Power Supply	Notes
DFT				
L1_TSTCLK	AC25	I	OV_{DD}	25
L2_TSTCLK	AE22	I	OV_{DD}	25
$\overline{\text{LSSD\_MODE}}$	AH20	I	OV_{DD}	25
$\overline{\text{TEST\_SEL}}$	AH14	I	OV_{DD}	25
Thermal Management				
THERM0	AG1	—	—	14
THERM1	AH1	—	—	14
Power Management				
ASLEEP	AH18	O	OV_{DD}	9, 19, 29
Power and Ground Signals				
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	—	—	—
OV_{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV_{DD}	—
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5 V)	GV_{DD}	—

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
SENSEVSS	M16	—	—	13
Analog Signals				
MVREF	A18	I Reference voltage signal for DDR	MVREF	—
SD_IMP_CAL_RX	L28	I	200 Ω (±1%) to GND	—
SD_IMP_CAL_TX	AB26	I	100 Ω (±1%) to GND	—
SD_PLL_TPA	U26	O	AVDD_SRDS	24

Note: All note references in this table use the same numbers as those for Table 71. See Table 71 for the meanings of these notes.

the ground plane. Use ceramic chip capacitors with the highest possible self-resonant frequency. All traces must be kept short, wide and direct.



Note:
1. An 0805 sized capacitor is recommended for system initial bring-up.

Figure 60. SerDes PLL Power Supply Filter

Note the following:

- AV_{DD}_SRDS must be a filtered version of SV_{DD}.
- Signals on the SerDes interface are fed from the XV_{DD} power plane.

22.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the device system, and the device itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} pin of the device. These decoupling capacitors must receive their power from separate V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, LV_{DD}, and GND power planes in the PCB, utilizing short low impedance traces to minimize inductance. Capacitors must be placed directly under the device using a standard escape pattern as much as possible. If some caps are to be placed surrounding the part it must be routed with large trace to minimize the inductance.

These capacitors must have a value of 0.1 µF. Only ceramic SMT (surface mount technology) capacitors must be used to minimize lead inductance, preferably 0402 or 0603 sizes. Besides, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD}, planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors must have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They must also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON). However, customers must work directly with their power regulator vendor for best values, types and quantity of bulk capacitors.

22.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors must be used to minimize inductance. Connections from all capacitors to power and ground must be done with multiple vias to further reduce inductance.

as shown in Figure 63. If this is not possible, the isolation resistor allows future access to $\overline{\text{TRST}}$ in case a JTAG interface may need to be wired onto the system in future debug situations.

- No pull-up/pull-down is required for TDI, TMS, TDO, or TCK.

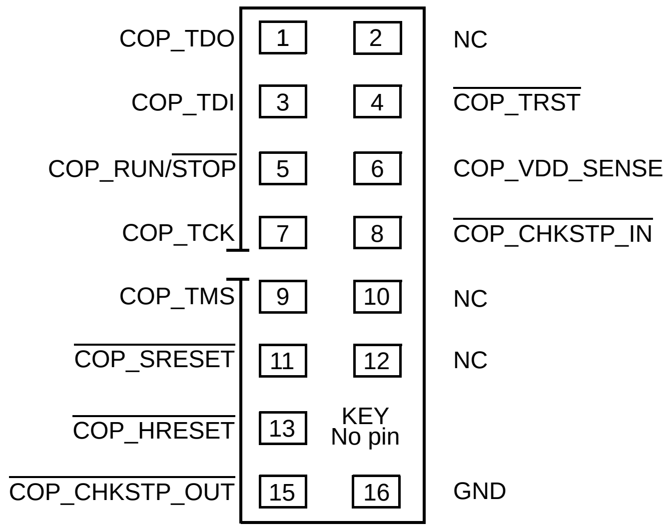


Figure 62. COP Connector Physical Pinout

22.10 Guidelines for High-Speed Interface Termination

This section provides the guidelines for high-speed interface termination when the SerDes interface is entirely unused and when it is partly unused.

22.10.1 SerDes Interface Entirely Unused

If the high-speed SerDes interface is not used at all, the unused pin must be terminated as described in this section.

The following pins must be left unconnected (float):

- SD_TX[7:0]
- $\overline{\text{SD\_TX}}$[7:0]
- Reserved pins T22, T23, M20, M21

The following pins must be connected to GND:

- SD_RX[7:0]
- $\overline{\text{SD\_RX}}$[7:0]
- SD_REF_CLK
- $\overline{\text{SD\_REF\_CLK}}$

NOTE

It is recommended to power down the unused lane through SRDSCR1[0:7] register (offset = 0xE_0F08) (This prevents the oscillations and holds the receiver output in a fixed state.) that maps to SERDES lane 0 to lane 7 accordingly.

Pins V28 and M26 must be tied to XV_{DD}. Pins V27 and M25 must be tied to GND through a 300-Ω resistor.

In Rev 2.0 silicon, POR configuration pin cfg_srds_en on TSEC4_TXD[2]/TSEC3_TXD[6] can be used to power down SerDes block.

22.10.2 SerDes Interface Partly Unused

If only part of the high-speed SerDes interface pins are used, the remaining high-speed serial I/O pins must be terminated as described in this section.

The following pins must be left unconnected (float) if not used:

- SD_TX[7:0]
- $\overline{\text{SD\_TX}}$[7:0]
- Reserved pins: T22, T23, M20, M21

The following pins must be connected to GND if not used:

- SD_RX[7:0]
- $\overline{\text{SD\_RX}}$[7:0]
- SD_REF_CLK

24 Document Revision History

The following table provides a revision history for this hardware specification.

Table 88. Document Revision History

Rev. Number	Date	Substantive Change(s)
9	02/2012	• Updated Section 21.2, "Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid," with version 3.0 silicon information. • Added Figure 56, "Mechanical Dimensions and Bottom Surface Nomenclature of the FC-PBGA with Stamped Lid." • Updated Table 87, "Part Numbering Nomenclature," with version 3.0 silicon information. • Removed Note from Section 5.1, "Power-On Ramp Rate". • Changed the Table 10 title to "Power Supply Ramp Rate". • Removed table 11. • Updated the title of Section 21.2, "Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid" to include Thermal Version 2.1.3 and Version 3.1.x Silicon. • Corrected the leaded Solder Ball composition in Table 70, "Package Parameters" • Updated Table 87, "Part Numbering Nomenclature," with Version 3.1.x silicon information. • Updated the Min and Max value of TDO in the valid times row of Table 44, "JTAG AC Timing Specifications (Independent of SYSCLK)[1]" from 4 and 25 to 2 and 10 respectively .
8	04/2011	• Added Section 14.1, "GPOUT/GPIN Electrical Characteristics." • Updated Table 71, "MPC8548E Pinout Listing," Table 72, "MPC8547E Pinout Listing," Table 73, "MPC8545E Pinout Listing," and Table 74, "MPC8543E Pinout Listing," to reflect that the TDO signal is not driven during HRSET* assertion. • Updated Table 87, "Part Numbering Nomenclature" with Ver. 2.1.3 silicon information.
7	09/2010	• In Table 37, "MII Management AC Timing Specifications, modified the fifth row from "MDC to MDIO delay tMDKHDX (16 × tptb_clk × 8) – 3 — (16 × tptb_clk × 8) + 3" to "MDC to MDIO delay tMDKHDX (16 × tCCB × 8) – 3 — (16 × tCCB × 8) + 3." • Updated Figure 55, "Mechanical Dimensions and Bottom Surface Nomenclature of the HiCTE FC-CBGA and FC-PBGA with Full Lid and figure notes.
6	12/2009	• In Section 5.1, "Power-On Ramp Rate" added explanation that Power-On Ramp Rate is required to avoid falsely triggering ESD circuitry. • In Table 13 changed required ramp rate from 545 V/s for MVREF and VDD/XVDD/SVDD to 3500 V/s for MVREF and 4000 V/s for VDD. • In Table 13 deleted ramp rate requirement for XVDD/SVDD. • In Table 13 footnote 1 changed voltage range of concern from 0–400 mV to 20–500mV. • In Table 13 added footnote 2 explaining that VDD voltage ramp rate is intended to control ramp rate of AVDD pins.
5	10/2009	• In Table 27, "GMII Receive AC Timing Specifications," changed duty cycle specification from 40/60 to 35/75 for RX_CLK duty cycle. • Updated tMDKHDX in Table 37, "MII Management AC Timing Specifications." • Added a reference to Revision 2.1.2. • Updated Table 55, "MII Management AC Timing Specifications." • Added Section 5.1, "Power-On Ramp Rate."